### MSC50DC170HJ

### Datasheet

# SiC Diode Full Bridge Power Module

December 2019



а <u> Міскосні</u>р company



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## 1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

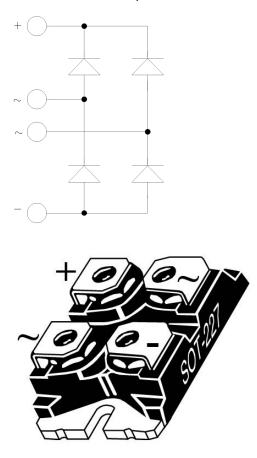
### 1.1 Revision 1.0

Revision 1.0 was published in December 2019. It is the first publication of this document.



## 2 Product Overview

This section shows the product overview of the MSC50DC170HJ device.



All ratings at  $T_i = 25^{\circ}$ C, unless otherwise specified.

**Caution:** These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

#### 2.1 Features

The following are key features of the MSC50DC170HJ device:

- Silicon Carbide (SiC) Schottky diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature-independent switching behavior
  - Positive temperature coefficient on VF
- Very low stray inductance
- High level of integration

#### 2.2 Benefits

The following are benefits of the MSC50DC170HJ device:



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

### 2.3 Applications

The MSC50DC170HJ device is designed for the following applications:

- Switch-mode power supplies rectifier
- Induction heating
- Welding equipment
- High-speed rectifiers



## 3 Electrical Specifications

This section shows the electrical specifications of the MSC50DC170HJ device.

### 3.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSC50DC170HJ device.

#### Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Max Ratings	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	1700	V	
I <sub>F</sub>	DC forward current	T <sub>C</sub> = 100 °C	50	A

#### Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
V <sub>ISOL</sub>	RMS isolation volt- age, any terminal to case t =1 minute, 50 Hz/60 Hz	2500			V
T <sub>J</sub> , T <sub>STG</sub>	Storage tempera- ture range	-55		175	°C
T <sub>JOP</sub>	Recommended junction tempera- ture under switch- ing conditions	-55		T <sub>Jmax</sub> – 25	
Torque	Terminals and mounting screws			1.1	N.m
Wt	Package weight		29.2		g

#### **3.2** Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSC50DC170HJ.

#### Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 50 A	T <sub>j</sub> = 25 °C		1.5	1.8	V
			T <sub>j</sub> = 175 °C		2		
I <sub>RM</sub>	Reverse leakage current	V <sub>R</sub> = 1700 V	T <sub>j</sub> = 25 °C		50	200	μΑ
			T <sub>j</sub> = 175 °C		250		
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 900 V			410		nC



Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
С	Total capacitance	f = 1 MHz, VR = 600 V		300		pF
		f = 1 MHz, VR = 900 V		250		
R <sub>thJC</sub>	Junction-to-case thermal resis			0.544	°C/W	



### 3.3 Typical Performance Curves

This section shows the typical performance curves of the MSC50DC170HJ device.

Figure 1 • Maximum Transient Thermal Impedance

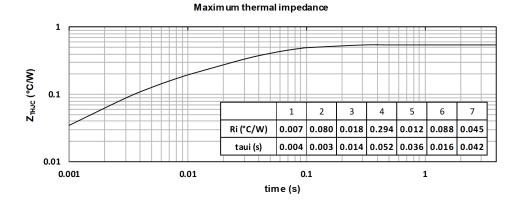


Figure 2 • Forward Current vs. Forward Voltage

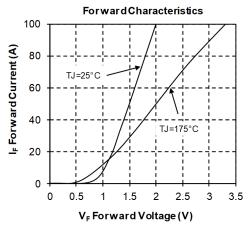
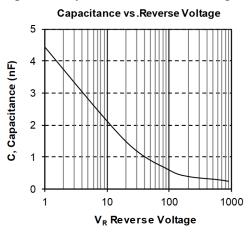


Figure 3 • Capacitance vs. Reverse Voltage



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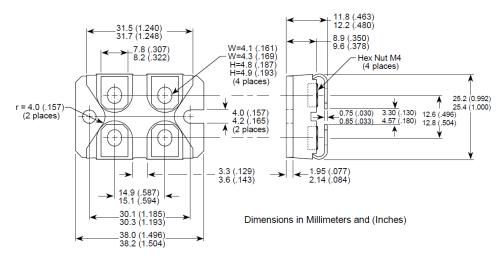
## 4 Package Specification

This section shows the package specification of the MSC50DC170HJ device.

### 4.1 Package Outline Drawing

The following image illustrates the package outline of MSC50DC170HJ device.

#### Figure 4 • Package Outline Drawing







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